

Triacs sensitive gate

BT137-600E

BT137 series E

GENERAL DESCRIPTION

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

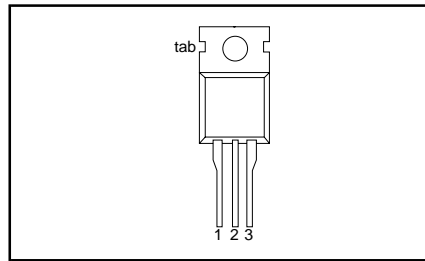
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.		UNIT
		600E	800E	
V_{DRM}	Repetitive peak off-state voltages	600	800	V
$I_{T(RMS)}$	RMS on-state current	8	8	A
I_{TSM}	Non-repetitive peak on-state current	65	65	A

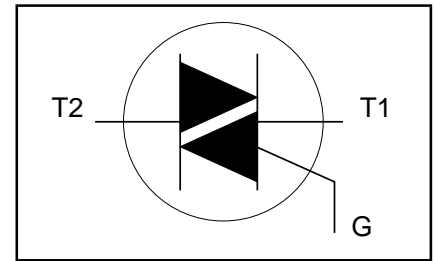
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				-600 600 ¹	-800 800	
V_{DRM}	Repetitive peak off-state voltages		-			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102^\circ\text{C}$	-	8		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ\text{C}$ prior to surge $t = 20\text{ ms}$	-	65		A
		$t = 16.7\text{ ms}$	-	71		A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	21		A ² s
di_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 12\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-			
		T2+ G+	-	50		A/ μs
		T2+ G-	-	50		A/ μs
		T2- G-	-	50		A/ μs
		T2- G+	-	10		A/ μs
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5		W
T_{stg}	Storage temperature		-40	150		$^\circ\text{C}$
T_j	Operating junction temperature		-	125		$^\circ\text{C}$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ μs .

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	2.0	K/W
$R_{th\ j-a}$		half cycle	-	-	2.4	K/W
	Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
I_{GT}	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	T2+ G+	-	2.5	10	mA
			T2+ G-	-	4.0	10	mA
			T2- G-	-	5.0	10	mA
			T2- G+	-	11	25	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	T2+ G+	-	3.0	25	mA
			T2+ G-	-	14	35	mA
			T2- G-	-	3.0	25	mA
			T2- G+	-	4.0	35	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	2.5	20	mA	
V_T	On-state voltage	$I_T = 10\text{ A}$	-	1.3	1.65	V	
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7	1.5	V	
I_D	Off-state leakage current	$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V	
		$V_D = V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA	

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ exponential waveform; gate open circuit	-	50	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 12\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

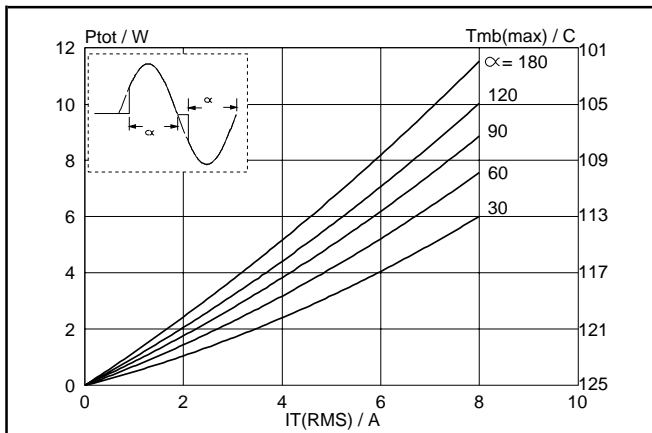


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

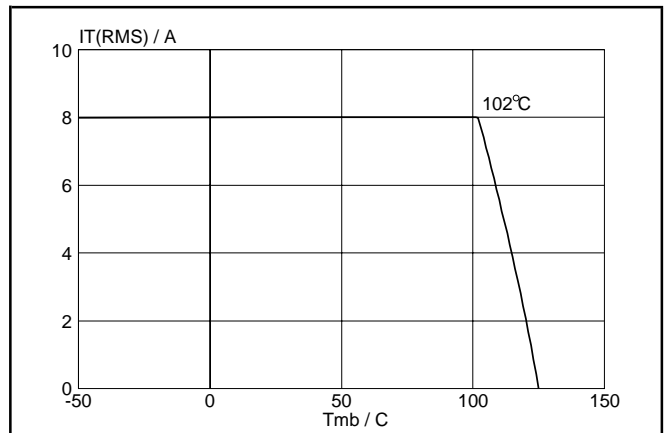


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

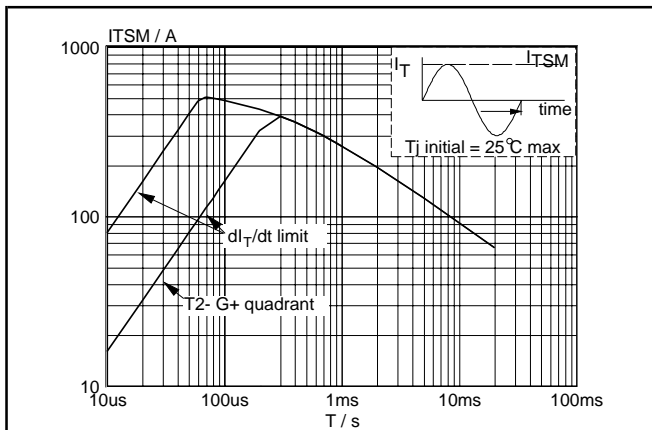


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20$ ms.

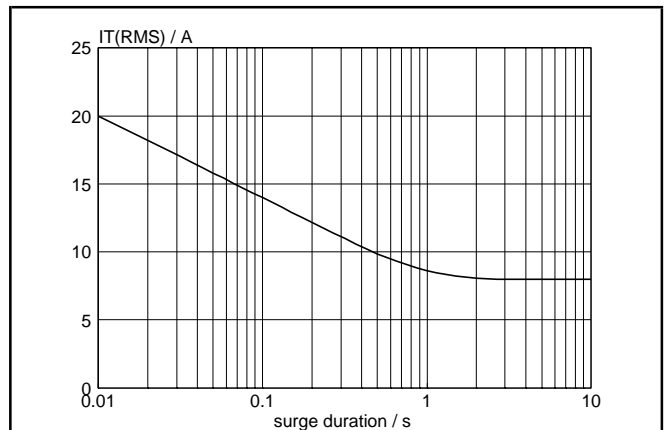


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50$ Hz; $T_{mb} \leq 102^\circ\text{C}$.

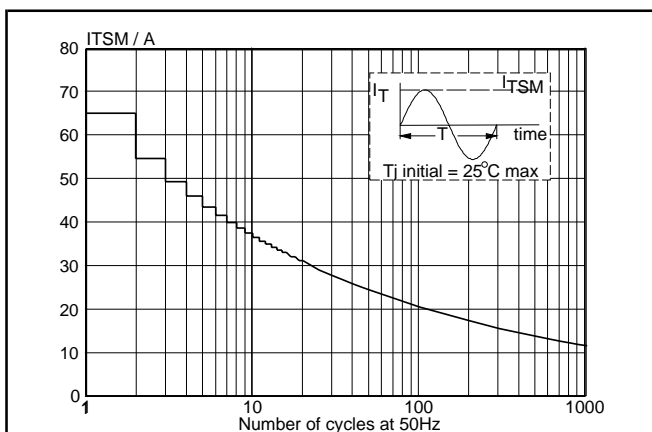


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50$ Hz.

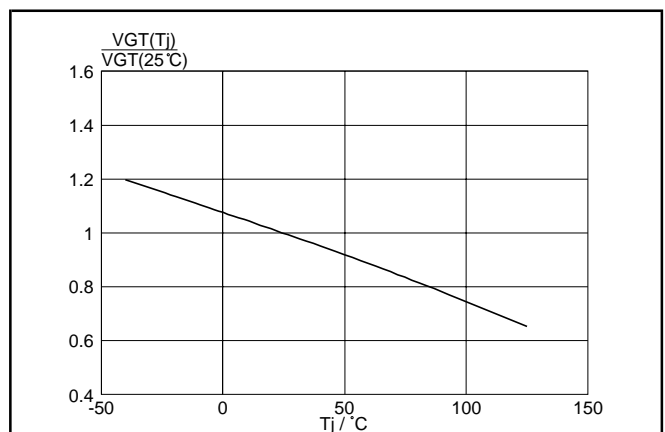


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

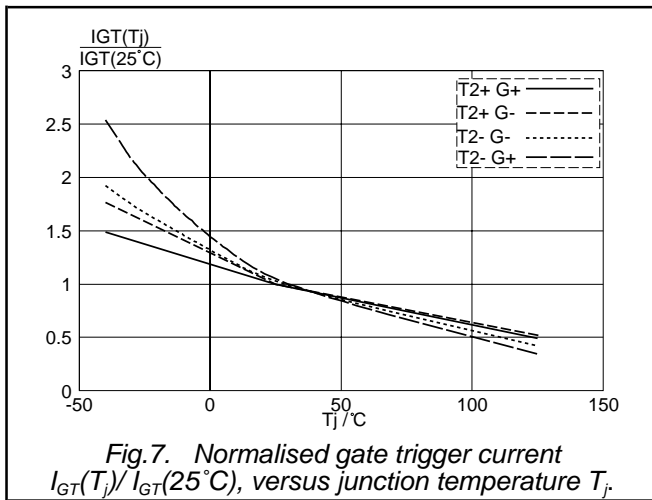


Fig. 7. Normalised gate trigger current $I_{GT}(T_j) / I_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

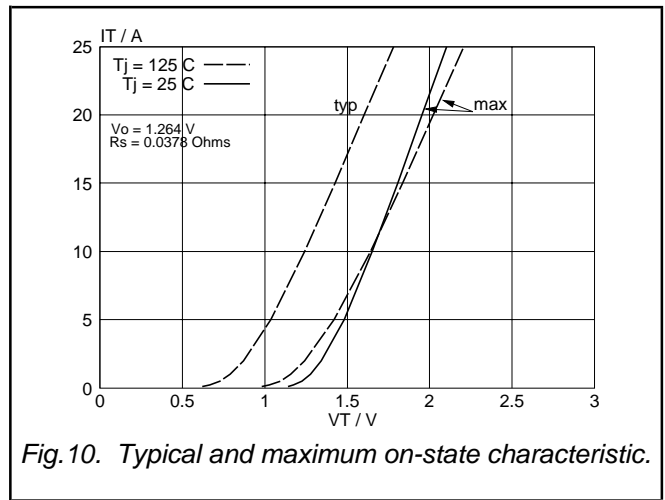


Fig. 10. Typical and maximum on-state characteristic.

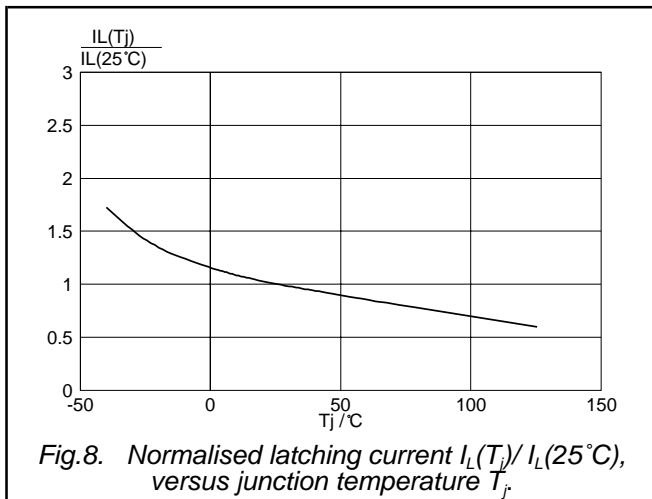


Fig. 8. Normalised latching current $I_L(T_j) / I_L(25^\circ\text{C})$, versus junction temperature T_j .

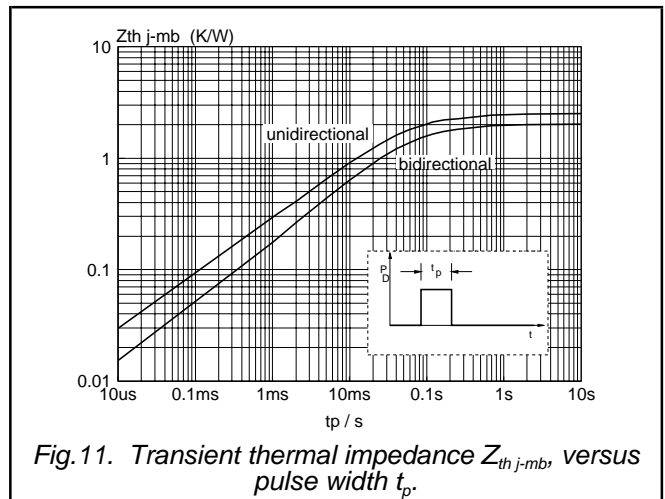


Fig. 11. Transient thermal impedance $Z_{th\ j-mb}$, versus pulse width t_p .

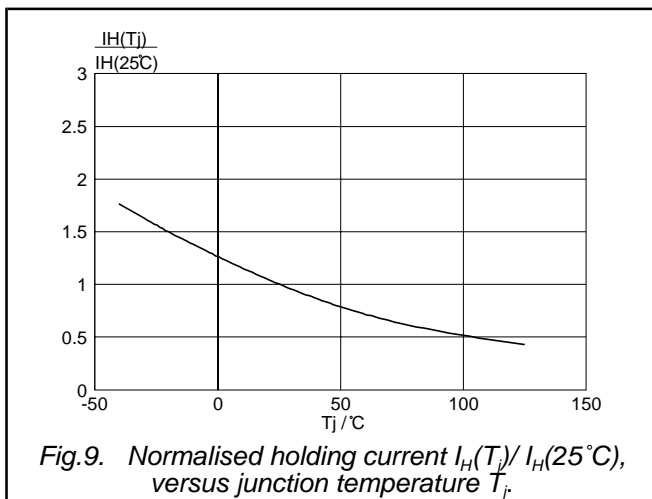


Fig. 9. Normalised holding current $I_H(T_j) / I_H(25^\circ\text{C})$, versus junction temperature T_j .

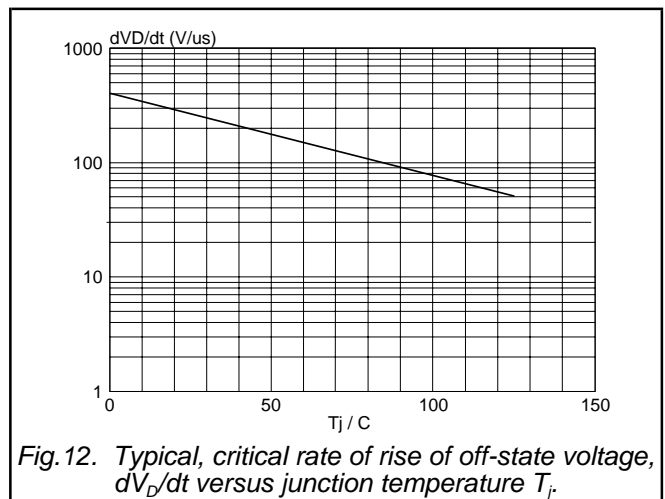
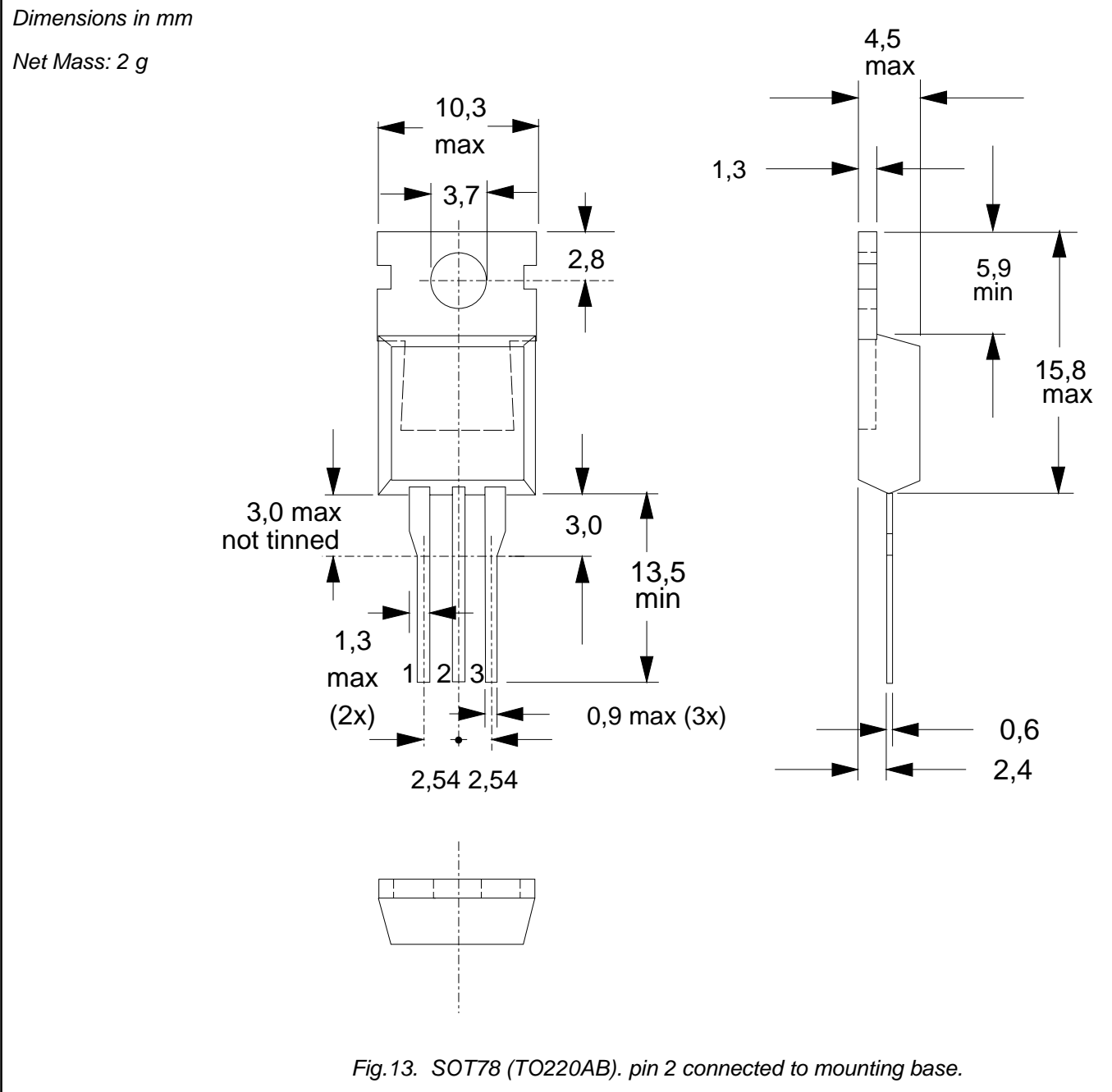


Fig. 12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j .

MECHANICAL DATA



- Notes**
1. Refer to mounting instructions for SOT78 (TO220) envelopes.
 2. Epoxy meets UL94 V0 at 1/8".